

# Phase Control Thyristors (Hockey PUK Version), 500 A



A-PUK (TO-200AB)

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	500 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 600 V				
V <sub>TM</sub>	1.35 V				
I <sub>GT</sub>	90 mA				
TJ	-40 °C to +150 °C				
Package	A-PUK (TO-200AB)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)



- Extended temperature range
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		500	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	80	°C			
1		1130	Α			
I <sub>T</sub> (RMS)	T <sub>hs</sub>	25	°C			
1	50 Hz	7200	A			
ITSM	60 Hz	7500	A			
l <sup>2</sup> t	50 Hz	260	kA <sup>2</sup> s			
I-I	60 Hz	230	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V			
tq	Typical	100	μs			
TJ		-40 to 150	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{array}{l} I_{DRM}/I_{RRM} \ MAXIMUM \\ AT \ T_J = T_J \ MAXIMUM \\ mA \end{array}$			
VS-ST280CHC	04	400	500	75			
V3-31200CHC	06	600	700	75			



ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	<b>L</b>	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	double side (single side) cooled			°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink temp	erature double side cooled	1130	
		t = 10 ms	No voltage		7200	
Maximum peak, one-cycle	<b>L</b>	t = 8.3 ms	reapplied		7500	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave, initial $T_J = T_J$ maximum	6000	
		t = 8.3 ms	reapplied		6300	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage reapplied		260	
		t = 8.3 ms			235	
		t = 10 ms			180	
		t = 8.3 ms	reapplied		165	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no voltage reapplied			2600	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.84	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.47	1115.2
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 1000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.35	V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada aunnis 1	2 V registive lead	600	mA
Maximum (typical) latching current	ΙL	1 J = 25 °C,	anoue supply 1	2 V resistive load	1000 (300)	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d$ 0.67 % $V_{DRM}$ , $T_J = 25 ^{\circ}C$	1.0	- 19
Typical turn-off time	t <sub>q</sub>	$\begin{array}{l} I_{TM}=300~A,~T_J=T_J~maximum,~dl/dt=20~A/\mu s,\\ V_R=50~V,~dV/dt=20~V/\mu s,~gate~0~V~100~\Omega,~t_p=500~\mu s \end{array}$	100	μs

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNIT S		
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs		
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	75	mA		



TRIGGERING							
PARAMETER	SYMBOL	TE	TEGT CONDITIONS			UNITS	
PANAMETEN	STINIBUL	''	ST CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	W	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J \text{ maximum, } t_p \le 5 \text{ ms}$		0	V		
Maximum peak negative gate voltage	- V <sub>GM</sub>	rj = rj maximum,	5.0				
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C		180	-		
DC gate current required to trigger		T <sub>J</sub> = 25 °C		90	150	mA	
		T <sub>J</sub> = 150 °C	T <sub>J</sub> = 150 °C Maximum required gate trigger/ current/voltage are the lowest		-		
		T <sub>J</sub> = - 40 °C	value which will trigger all units 12 V anode to cathode applied	2.9	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 v anode to cathode applied	1.8	3.0	V	
	T <sub>J</sub> = 150 °C		1.0	-			
DC gate current not to trigger	I <sub>GD</sub>	T. T. magyimay	Maximum gate current/voltage not to trigger is the maximum	1	0	mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.	30	V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 150	°C		
Maximum thermal resistance,	В	DC operation single side cooled	0.17			
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.08	K/W		
Maximum thermal resistance,	В	DC operation single side cooled	0.033	T N VV		
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.017			
Mounting force, ± 10 %			4900 (500)	N (kg)		
Approximate weight			50	g		
Case style		See dimensions - link at the end of datasheet	A-PUK (TO-2	200AB)		

$\Delta R_{thJ-hs}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.016	0.017	0.011	0.011	$T_J = T_J$ maximum	
120°	0.019	0.019	0.019	0.019		K/W
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC





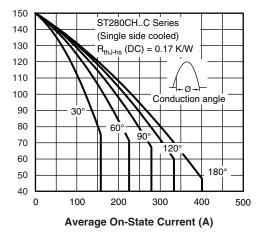


Fig. 1 - Current Ratings Characteristics

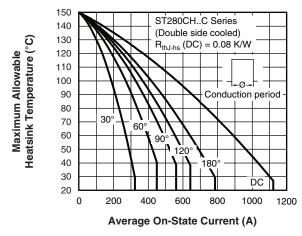


Fig. 4 - Current Ratings Characteristics

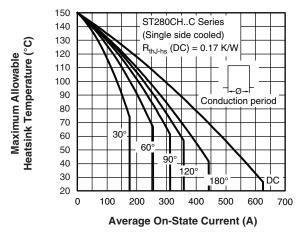


Fig. 2 - Current Ratings Characteristics

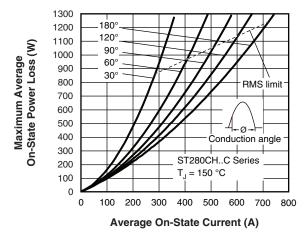


Fig. 5 - On-State Power Loss Characteristics

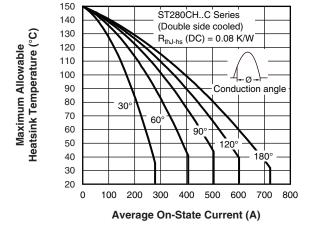


Fig. 3 - Current Ratings Characteristics

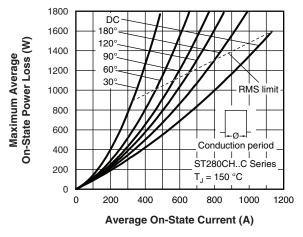


Fig. 6 - On-State Power Loss Characteristics

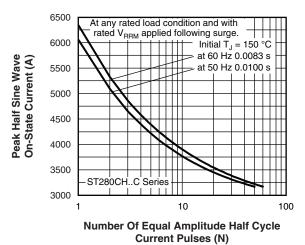


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

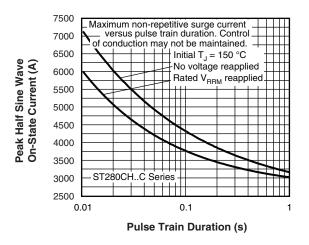


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

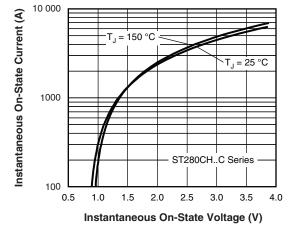


Fig. 9 - On-State Voltage Drop Characteristics

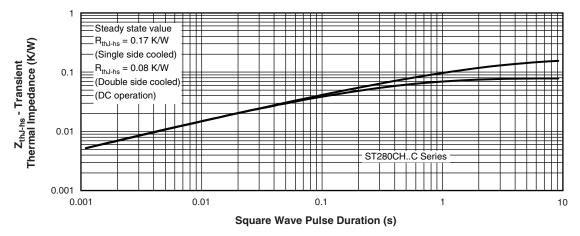


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

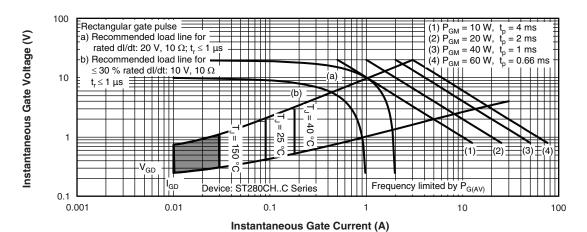
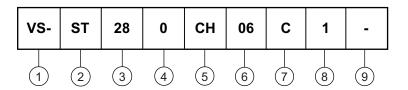


Fig. 11 - Gate Characteristics

## ORDERING INFORMATION TABLE

#### Device code



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - CH = ceramic PUK, high temperature

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - C = PUK case A-PUK (TO-200AB)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

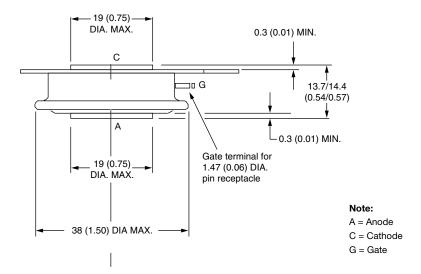
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95074		

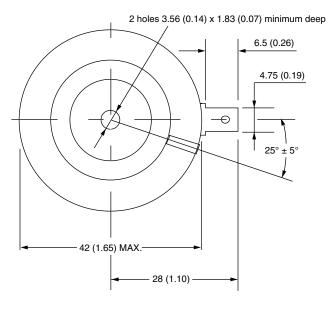


# **A-PUK (TO-200AB)**

#### **DIMENSIONS** in millimeters (inches)

Anode to gate Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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